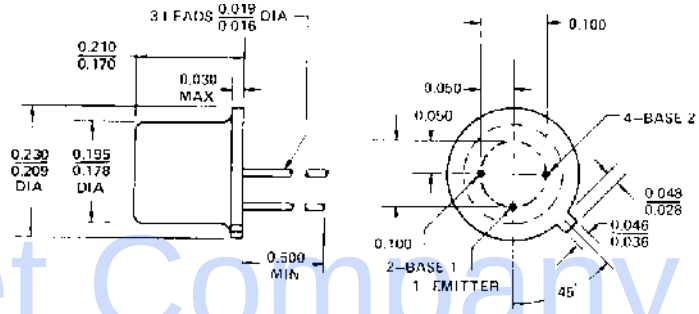
SILICON PN UNIJUNCTION TRANSISTOR

DESCRIPTION:

The **2N2646** is a Unijunction Transistor Used in General Purpose Pulse, Timing, Sense and Trigger Applications.

PACKAGE STYLE TO-18 (MOD)



MAXIMUM RATINGS

I_C	2.0 A (PULSED)
V_{CE}	30 V
P_{DISS}	300 mW @ T_C = 25 °C
T_J	-65 °C to +125 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	33 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
η	V_{B2B1} = 10 V	0.56		0.75	--
r_{BB}	V_{B2B1} = 3.0 V	4.7		9.1	KΩ
α_{rBB}	V_{B2B1} = 3.0 V T_A = -55 to 125°C	0.1		0.9	%/°C
$V_{EB1(SAT)}$	V_{B2B1} = 10 V I_E = 50 mA		3.0		V
$I_{B2(MOD)}$	V_{B2B1} = 10 V I_E = 50 mA		20		mA
I_{B2EO}	V_{B2E} = 30 V I_{B1} = 0			12	µA
I_P	V_{B2B1} = 25 V			5.0	µA
I_V	V_{B2B1} = 20 V R_{B2} = 100 Ω	4.0			mA
V_{OB1}	V_{B2B1} = 20 V R_{B1} = 20 Ω	3.0	5.0		V